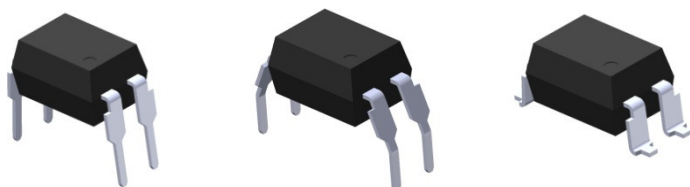
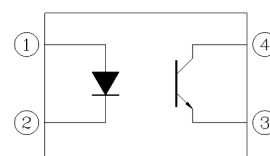


4 PIN DIP HIGH VOLTAGE PHOTOTRANSISTOR PHOTOCOUPLER EL851 Series



Schematic



Pin Configuration

1. Anode
2. Cathode
3. Emitter
4. Collector

Features:

- High collector- emitter voltage ($V_{CEO}=350V$)
- Current transfer ratio
(CTR: 50~600% at $I_F=5mA$, $V_{CE}=5V$)
- High isolation voltage between input and output ($V_{iso}=5000 V_{rms}$)
- Compact dual-in-line package
- Pb free and RoHS compliant.
- UL approved (No. E214129)
- VDE approved (No. 132249)
- SEMKO approved
- NEMKO approved
- DEMKO approved
- FIMKO approved

Description

The EL851 series devices consist an infrared emitting diodes, optically coupled to a phototransistor detector.

The devices are in a 4-pin DIP package and available in wide-lead spacing and SMD option.

Applications

- Telephone line interface
- Interface to power supply circuit
- Controller for SSRs. DC motor
- Programmable Controllers

Absolute Maximum Ratings (Ta=25°C)

	Parameter	Symbol	Rating	Unit
Input	Forward current	I_F	60	mA
	Peak forward current (1μs pulse)	I_{FM}	1	A
	Reverse voltage	V_R	6	V
	Power dissipation	P_D	100	mW
Output	Collector power dissipation	P_C	150	mW
	Collector-Emitter voltage	V_{CEO}	350	V
	Collector Current	I_C	50	mA
	Emitter-Collector voltage	V_{ECO}	7	V
Total Power Dissipation		P_{TOT}	200	mW
Isolation Voltage* ¹		V_{ISO}	5000	V rms
Operating Temperature		T_{OPR}	-55 to 100	°C
Storage Temperature		T_{STG}	-55 to 125	°C
Soldering Temperature* ²		T_{SOL}	260	°C

Notes:

*1 AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1, 2 are shorted together, and pins 3, 4 are shorted together.

*2 For 10 seconds

Electro-Optical Characteristics (Ta=25°C unless specified otherwise)

Input

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage	V_F	-	1.2	1.4	V	$I_F = 10\text{mA}$
Reverse Current	I_R	-	-	10	μA	$V_R = 5\text{V}$
Input capacitance	C_{in}	-	30	250	pF	$V = 0, f = 1\text{kHz}$

Output

Parameter	Symbol	Min	Typ.	Max.	Unit	Condition
Collector-Emitter dark current	I_{CEO}	-	-	100	nA	$V_{CE} = 200\text{V}$
Collector-Emitter breakdown voltage	BV_{CEO}	350	-	-	V	$I_C = 0.1\text{mA}$
Emitter-Collector breakdown voltage	BV_{ECO}	7	-	-	V	$I_E = 0.1\text{mA}$
Collector-Emitter capacitance	C_{CE}	-	10	-	pF	$V_{CE} = 0\text{V}, f = 1\text{MHz}$

Transfer Characteristics

Parameter	Symbol	Min	Typ.	Max.	Unit	Condition
Current Transfer Ratio	CTR	50	-	600	%	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	0.4	V	$I_F = 20\text{mA}, I_C = 1\text{mA}$
Isolation resistance	R_{IO}	10^{11}	-	-	Ω	$V_{IO} = 500\text{Vdc}$
Input-output capacitance	C_{IO}	-	0.6	-	pF	$V_{IO} = 0, f = 1\text{MHz}$
Rise time	t_r	-	4	18	μs	$V_{CE} = 2\text{V}, I_C = 2\text{mA}, R_L = 100\Omega$
Fall time	t_f	-	5	18	μs	

* Typical values at $T_a = 25^\circ\text{C}$

Typical Electro-Optical Characteristics Curves

Figure 1. Forward Current vs Forward Voltage

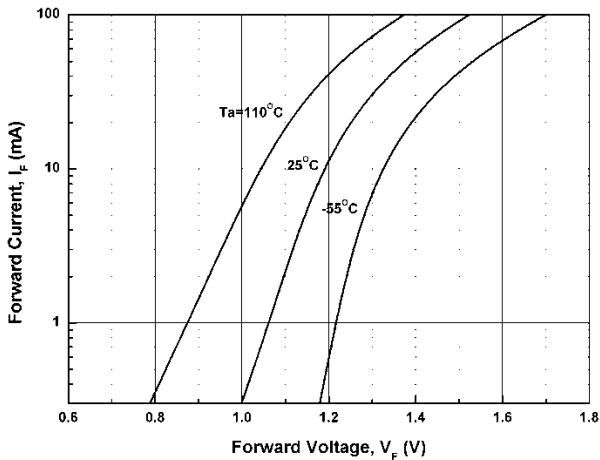


Figure 2. Current Transfer Ratio vs Forward Current

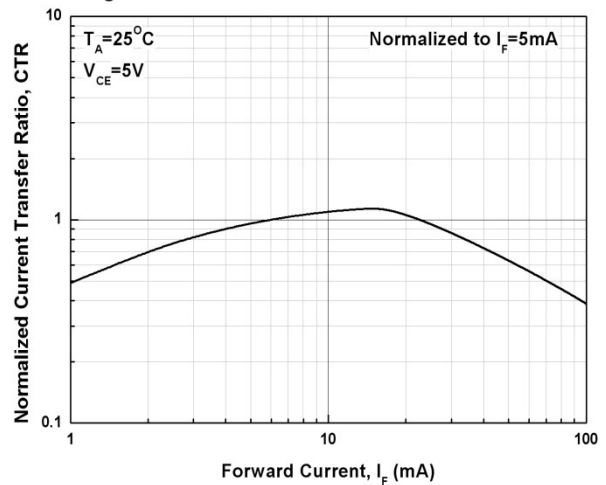


Figure 3. Collector Current vs Collector-emitter Voltage

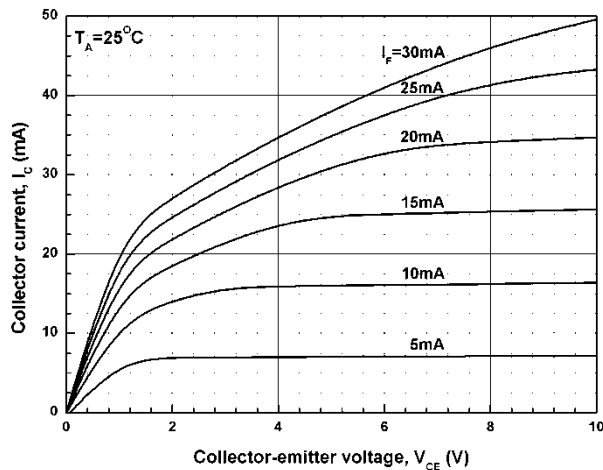


Figure 4. Relative Current Transfer Ratio vs Ambient Temperature

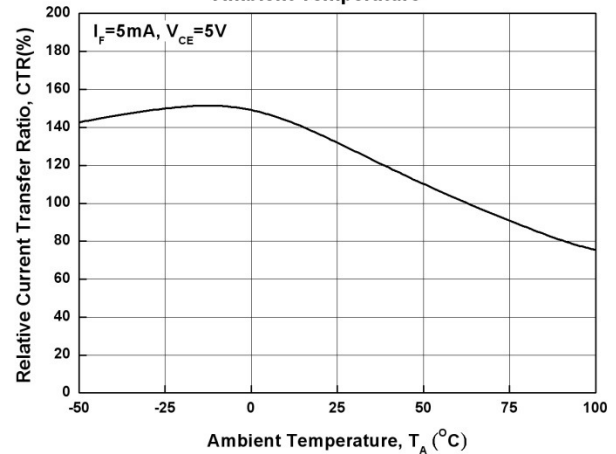


Figure 5. Collector-emitter Saturation Voltage vs Ambient Temperature

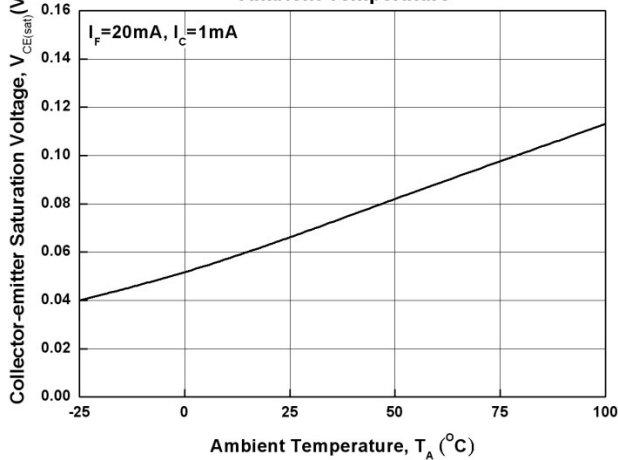


Figure 6. Dark Current vs Ambient Temperature

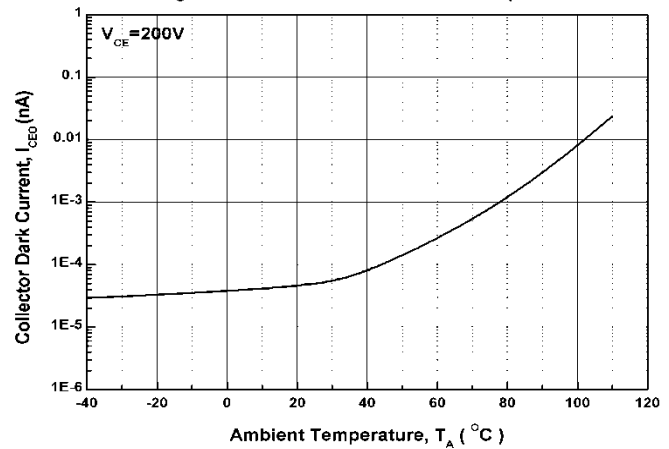


Figure .7 Switching Time vs. Load Resistance

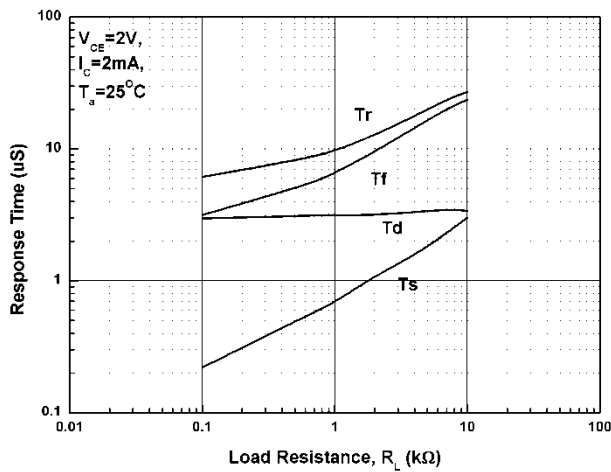


Figure 8. Collector-emitter Saturation Voltage vs Forward Current

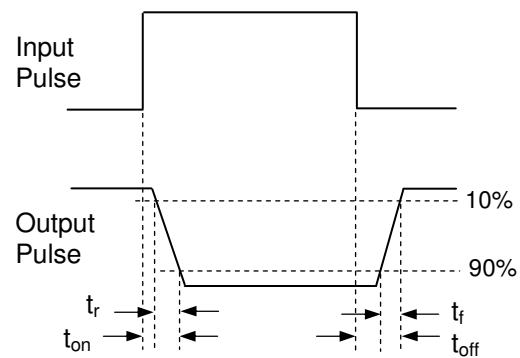
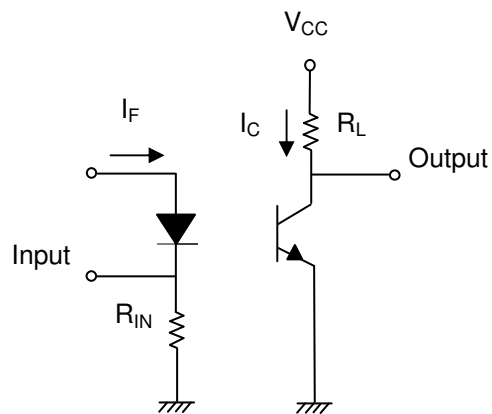
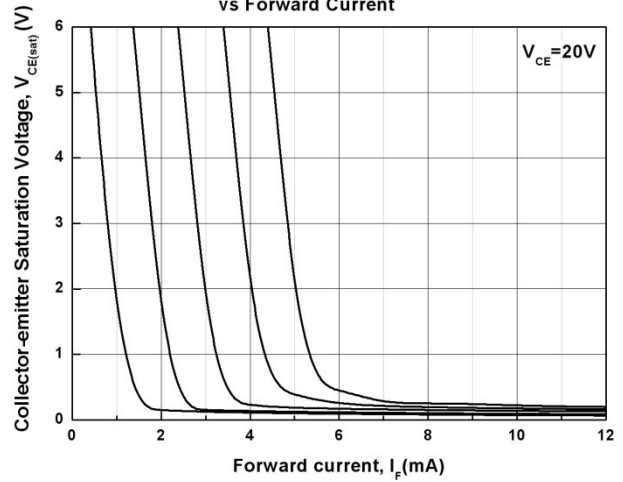


Figure 9. Switching Time Test Circuit & Waveforms

Order Information

Part Number

EL851X(Z)-V

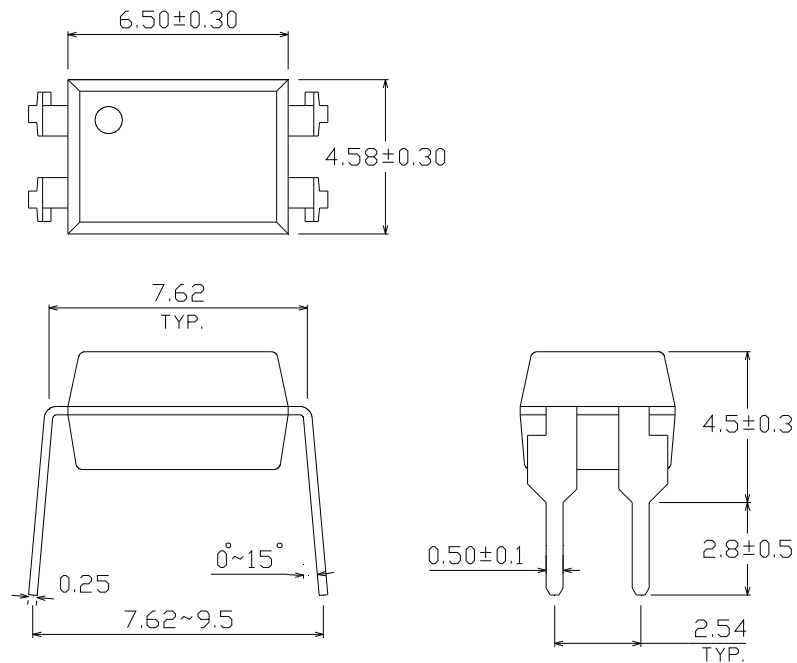
Note

- X = Lead form option (S, S1, M or none)
Z = Tape and reel option (TA, TB, TU, TD or none).
V = VDE safety (optional).

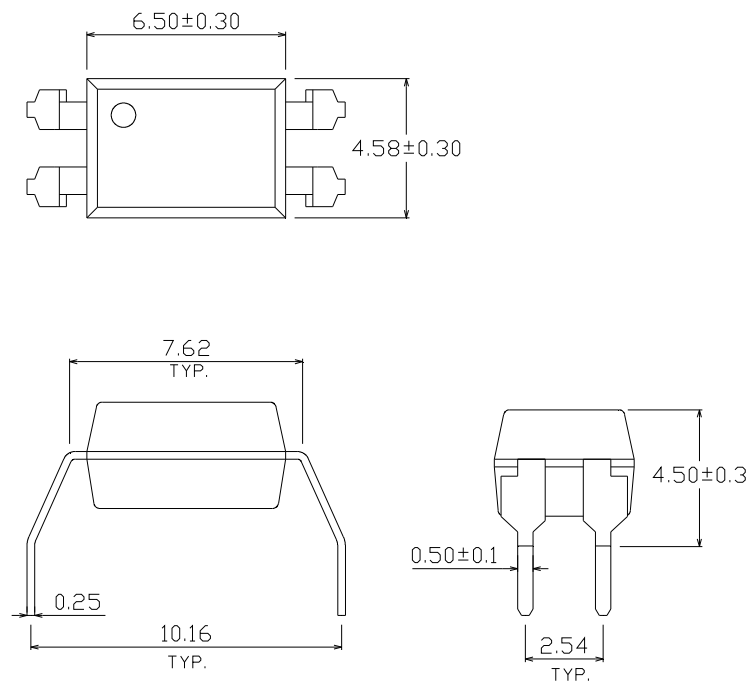
Option	Description	Packing quantity
None	Standard DIP-4	100 units per tube
M	Wide lead bend (0.4 inch spacing)	100 units per tube
S (TA)	Surface mount lead form + TA tape & reel option	1000 units per reel
S (TB)	Surface mount lead form + TB tape & reel option	1000 units per reel
S1 (TA)	Surface mount lead form (low profile) + TA tape & reel option	1000 units per reel
S1 (TB)	Surface mount lead form (low profile) + TB tape & reel option	1000 units per reel
S (TU)	Surface mount lead form + TU tape & reel option	1500 units per reel
S (TD)	Surface mount lead form + TD tape & reel option	1500 units per reel
S1 (TU)	Surface mount lead form (low profile) + TU tape & reel option	1500 units per reel
S1 (TD)	Surface mount lead form (low profile) + TD tape & reel option	1500 units per reel

Package Dimension (Dimensions in mm)

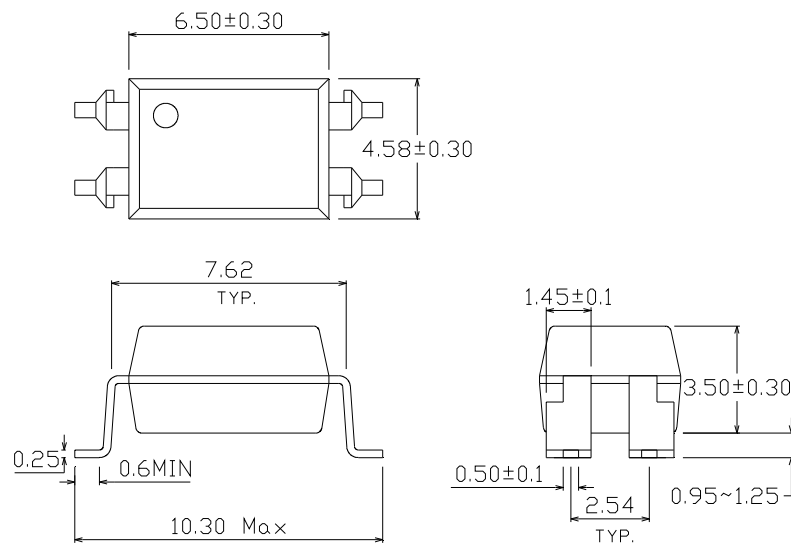
Standard DIP Type



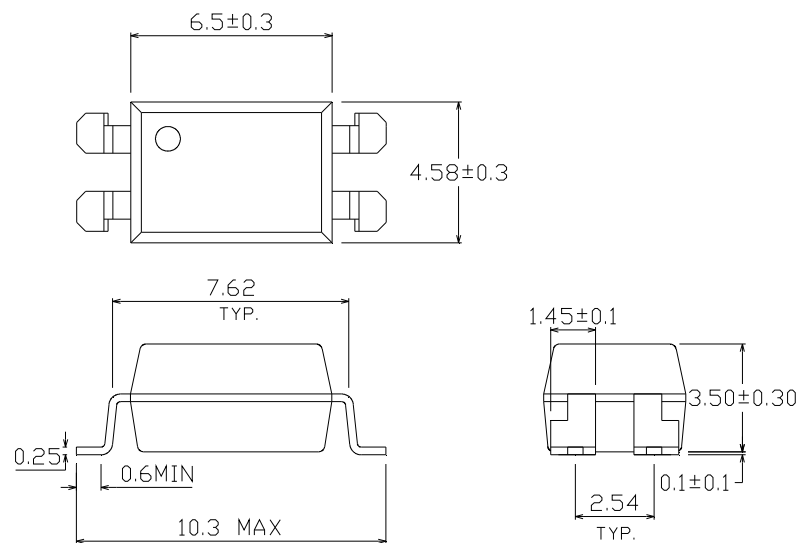
Option M Type



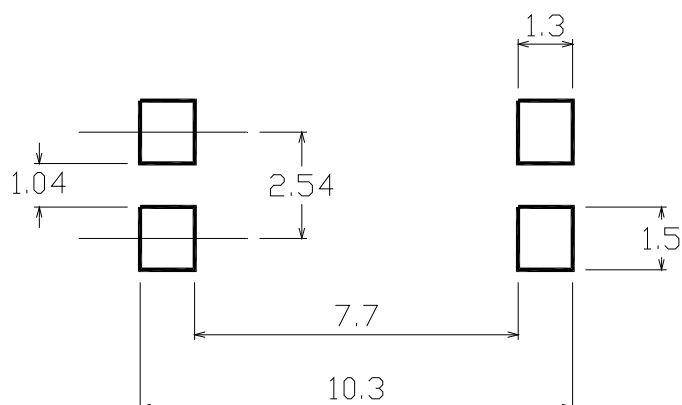
Option S Type



Option S1 Type



Recommended pad layout for surface mount leadform



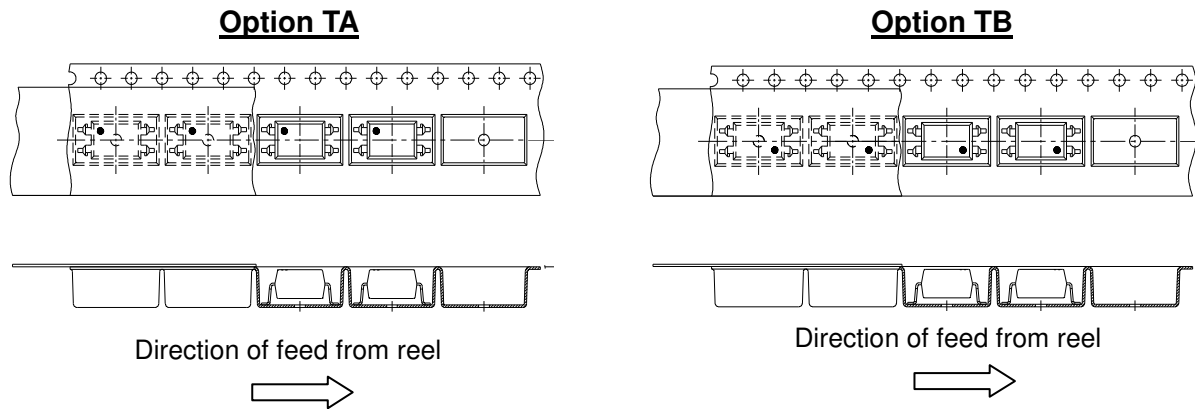
Device Marking



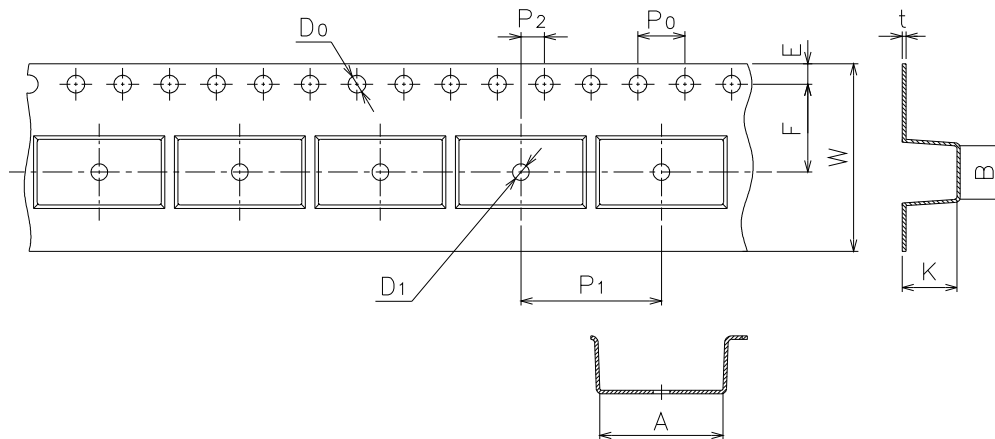
Notes

EL	denotes EVERLIGHT
851	denotes Device Number
Y	denotes 1 digit Year code
WW	denotes 2 digit Week code
V	denotes VDE (optional)

Tape & Reel Packing Specifications



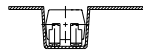
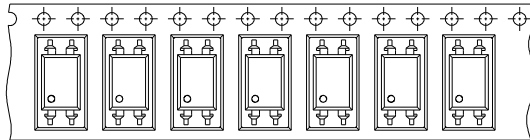
Tape dimensions



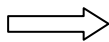
Dimension No.	A	B	Do	D1	E	F
Dimension (mm) S	10.5±0.1	4.65±0.1	1.5±0.1	1.50±0.1	1.75±0.1	7.5±0.1
Dimension (mm) S1	10.5±0.1	4.65±0.1	1.5±0.1	1.50±0.1	1.75±0.1	7.5±0.1
Dimension No.	Po	P1	P2	t	W	K
Dimension (mm) S	4.0±0.1	12.0±0.1	2.0±0.1	0.4±0.1	16.0±0.3	5.05±0.1
Dimension (mm) S1	4.0±0.1	12.0±0.1	2.0±0.1	0.4±0.1	16.0±0.3	4.75±0.1

Tape & Reel Packing Specifications

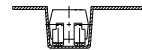
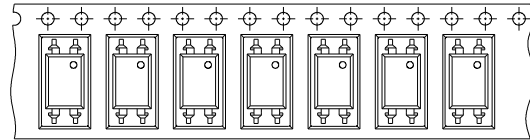
Option TD



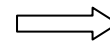
Direction of feed from reel



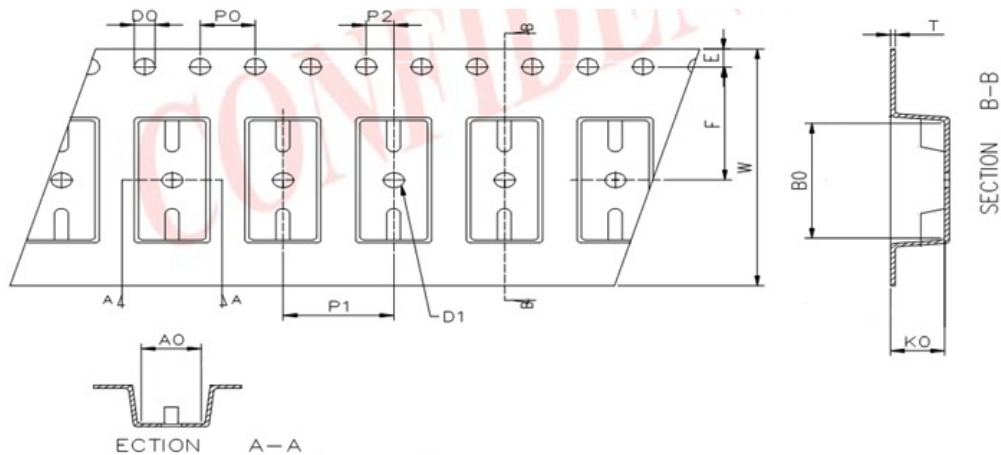
Option TU



Direction of feed from reel



Tape dimensions

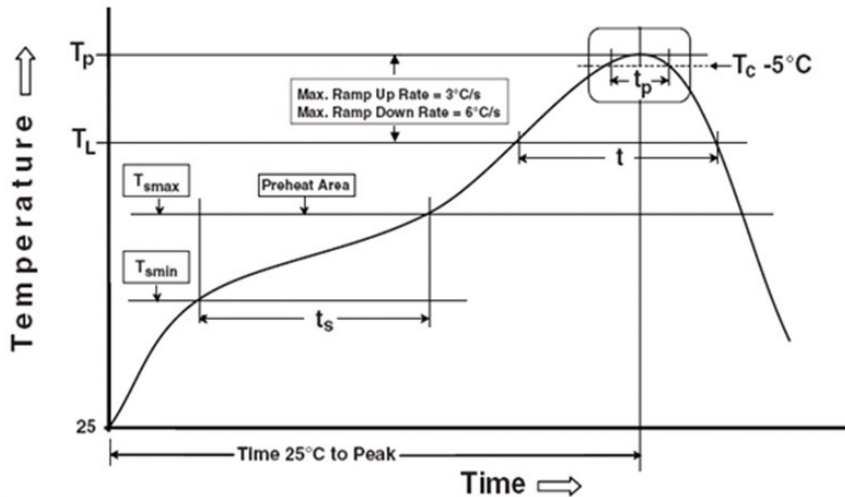


Dimension No.	Ao	Bo	Do	D1	E	F
Dimension (mm)	4.90±0.1	10.40±0.1	1.5±0.1	1.50±0.1	1.75±0.1	7.50±0.1
Dimension No.	Po	P1	P2	t	W	Ko
Dimension(mm)	4.00±0.1	8.00±0.	2.00±0.1	0.40±0.1	16.00±0.3	4.60±0.1

Precautions for Use

1. Soldering Condition

1.1 (A) Maximum Body Case Temperature Profile for evaluation of Reflow Profile



Note:

Reference: IPC/JEDEC J-STD-020D

Preheat

Temperature min (T_{smin})	150 °C
Temperature max (T_{smax})	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max

Other

Liquidus Temperature (T_L)	217 °C
Time above Liquidus Temperature (t_L)	60-100 sec
Peak Temperature (T_p)	260 °C
Time within 5 °C of Actual Peak Temperature: $T_p - 5^\circ\text{C}$	30 s
Ramp- Down Rate from Peak Temperature	6°C /second max.
Time 25°C to peak temperature	8 minutes max.
Reflow times	3 times

DISCLAIMER

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2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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